

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S2	1	"10706461"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 15:12
S3	169	257/325.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 15:52
S6	29	S3 and spacer	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/22 15:55
S7	7	10/423,637	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/22 16:08
S8	6	10/327,336	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/22 16:08
S17	2	60/239,467	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 16:21
S18	3	09/685,968	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 12:45
S19	7	09/502,628	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 12:49
S20	6	09/502,153	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 12:49

S21	6	09/502,375	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 12:50
S22	1	high adj refresh adj memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 15:58
S23	5395	high same refresh same memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 12:52
S24	197	(high same refresh same memory) and multi\$1layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 12:57
S25	19	(memory) and (multi\$1layer adj spacer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 13:20
S26	14	"6,069,042"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 12:59
S27	35594	(memory) and ((multi\$1layer adj spacer) or MLS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 13:21
S28	6	S25 and MLS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 13:21

S30	18350	gate adj oxide adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 14:03
S31	459	S30 and gate adj conductive adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 14:03
S32	313	S31 and semiconductor adj substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 14:03
S33	6	S32 and polyoxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 14:04
S34	5395	high same refresh same memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 15:59
S35	153	high adj refresh same memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 15:59
S36	4	S35 and spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 15:59
S37	82829	MOSFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 16:00

S38	1123	S37 and multi\$2layer\$2 and spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 16:00
S39	667	S38 and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/25 16:07
S44	460	257/900.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:37
S45	301	spacer and 257/900.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 08:33
S46	24	S45 and multi\$2layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 08:40
S47	24	S44 and multi\$1layer\$2 and sidewall and spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 08:49
S49	590	257/327.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 08:49
S50	153	S49 and spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 08:49
S56	4	("6040223"   "6071826"   "6165883"   "6329225").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/26 09:05

S64	287	257/311.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/26 09:23
S65	90	S64 and spacer	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/26 09:23
S67	1301	257/306.ccls.	USPAT	OR	ON	2005/07/26 09:52
S68	455	S67 and spacer	USPAT	OR	ON	2005/07/26 09:39
S69	171	S67 and spacer and multi\$6	USPAT	OR	ON	2005/07/26 09:41
S70	8	S67 and spacer with multi\$6	USPAT	OR	ON	2005/07/26 09:41
S71	21849	ONO	USPAT	OR	ON	2005/07/26 10:32
S72	2029	ONO and DRAM	USPAT	OR	ON	2005/07/26 09:52
S73	504	ONO and DRAM and multi	USPAT	OR	ON	2005/07/26 09:54
S74	196	ONO and DRAM and multi and spacer	USPAT	OR	ON	2005/07/26 09:55
S75	203	ONO and DRAM and multi\$1layer\$2 and spacer	USPAT	OR	ON	2005/07/26 10:20
S76	1	ONO and DRAM and multi\$1layer\$2 adj spacer	USPAT	OR	ON	2005/07/26 10:21
S77	6	ONO and multi\$1layer\$2 adj spacer	USPAT	OR	ON	2005/07/26 10:21
S79	2845	S71 and sidewall	USPAT	OR	ON	2005/07/26 10:32
S80	861	S71 and sidewall adj spacer	USPAT	OR	ON	2005/07/26 10:32
S81	376	S71 and sidewall adj spacer and DRAM	USPAT	OR	ON	2005/07/26 10:33
S82	0	S71 and triple adj sidewall adj spacer and DRAM	USPAT	OR	ON	2005/07/26 10:33
S83	0	S71 and multi\$2layer\$2 adj sidewall adj spacer and DRAM	USPAT	OR	ON	2005/07/26 10:34
S84	2	S71 and multi\$6 adj sidewall adj spacer and DRAM	USPAT	OR	ON	2005/07/26 10:35
S85	1	"5,712,202".pn.	USPAT	OR	ON	2005/07/26 10:35
S98	1	"6011725".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/26 15:20
S99	1	"5045486".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/26 15:28
S100	1	"5102816".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/26 15:28

S10 1	1416	ldd with mosfet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 16:30
S10 2	783	S101 and (three or third or triple)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 16:31
S10 3	426	S101 and ((three or third or triple) with layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 16:33
S10 4	226	S103 and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 16:38
S10 5	61	S103 and (memory near DRAM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 16:38
S11 2	654	(four or "4") adj layer same spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 08:37
S11 3	1226	438/230,265,595.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 09:15
S11 4	3372	257/325,306,311,327,900.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 16:19

S118	107	multi\$2layer\$2 adj spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 08:37
S120	9	S113 and S118	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 09:13
S130	162	S113 and ONO	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 09:15
S131	235	438/230.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 09:00
S132	240	438/265.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 09:06
S133	140	438/265.ccls. and spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 09:06
S136	5	S114 and S118	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 09:13
S137	2000	257/306.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 09:14

S13 8	303	257/311.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 09:14
S13 9	590	257/327.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 09:14
S14 0	460	257/900.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 08:29
S14 1	825	438/595.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 09:15
S14 2	1	S113 and ONON	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 09:15
S14 3	0	nitride adj external adj spacer and 257/325,306,311,327,900.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 12:53
S14 4	139	nitride adj spacer and 257/325,306, 311,327,900.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 12:53
S14 7	1226	438/230,265,595.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 16:19



S14 8	3372	257/325,306,311,327,900.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 16:21
S14 9	1172	257/390.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/27 16:21
S15 0	142	S149 and ONO	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 09:01
S15 1	2	"20020110966"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 09:40
S15 2	2	"6358864".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 09:03
S15 3	2	"5290720".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 09:04
S15 4	2	"20050040479".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 09:08
S16 0	2	"6727539".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 09:08

S16 2	7	"016983"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 09:41
S16 3	2	"01-6983"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:10
S16 4	388	dielectric adj constant near "3.9"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:10